



General Description

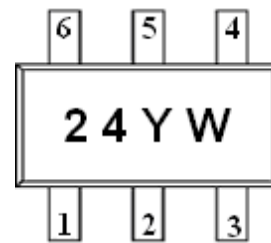
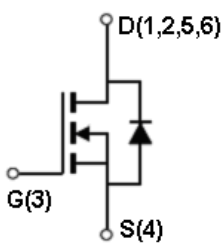
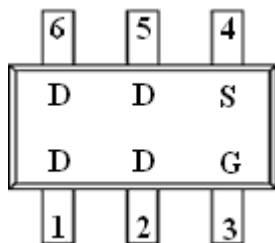
AFN1424, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 20V/5.0A, $R_{DS(ON)}=30m\Omega@V_{GS}=4.5V$
- 20V/3.2A, $R_{DS(ON)}=36m\Omega@V_{GS}=2.5V$
- 20V/2.4A, $R_{DS(ON)}=46m\Omega@V_{GS}=1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-363 package design

Pin Description (SOT-363)



Application

- Portable Equipment
- Battery Powered System
- Net Working System

Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN1424S36RG	24YW	SOT-363	Tape & Reel	3000 EA

- ※ 24 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFN1424S36RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C 4.0	A
		T _A =70°C 3.2	
Pulsed Drain Current	I _{DM}	10	A
Continuous Source Current(Diode Conduction)	I _S	0.9	A
Power Dissipation	P _D	T _A =25°C 1.0	W
		T _A =70°C 0.52	
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

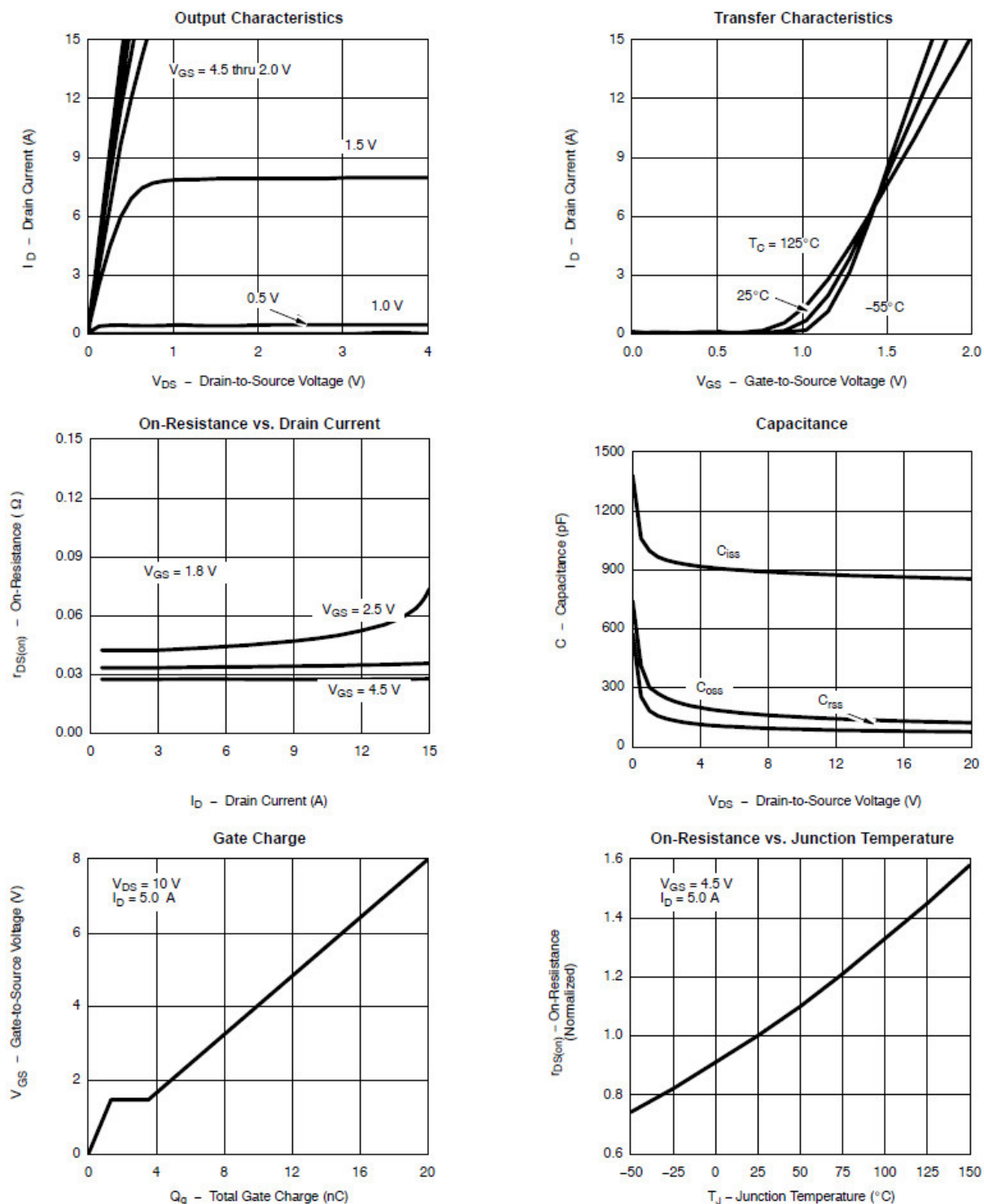
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.45		0.85	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	uA
		V _{DS} =16V, V _{GS} =0V T _J =85°C			10	
On-State Drain Current	I _{D(on)}	V _{DS} ≥5V, V _{GS} =4.5V	6			A
		V _{DS} ≥5V, V _{GS} =2.5V	4			
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =5.0A		25	30	mΩ
		V _{GS} =2.5V, I _D =3.2A		29	36	
		V _{GS} =1.8V, I _D =2.4A		37	46	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3.6A		10		S
Diode Forward Voltage	V _{SD}	I _S =1.6A, V _{GS} =0V		0.85	1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V I _D ≡4.0A		11	15	nC
Gate-Source Charge	Q _{gs}			1.2		
Gate-Drain Charge	Q _{gd}			2.5		
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V f=1MHz		600		pF
Output Capacitance	C _{oss}			205		
Reverse Transfer Capacitance	C _{rss}			60		
Turn-On Time	t _{d(on)}	V _{DD} =10V, R _L =5.5Ω I _D ≡4.0A, V _{GEN} =4.5V R _G =6Ω		15	25	ns
	t _r			40	60	
Turn-Off Time	t _{d(off)}			48	70	
	t _f			30	45	

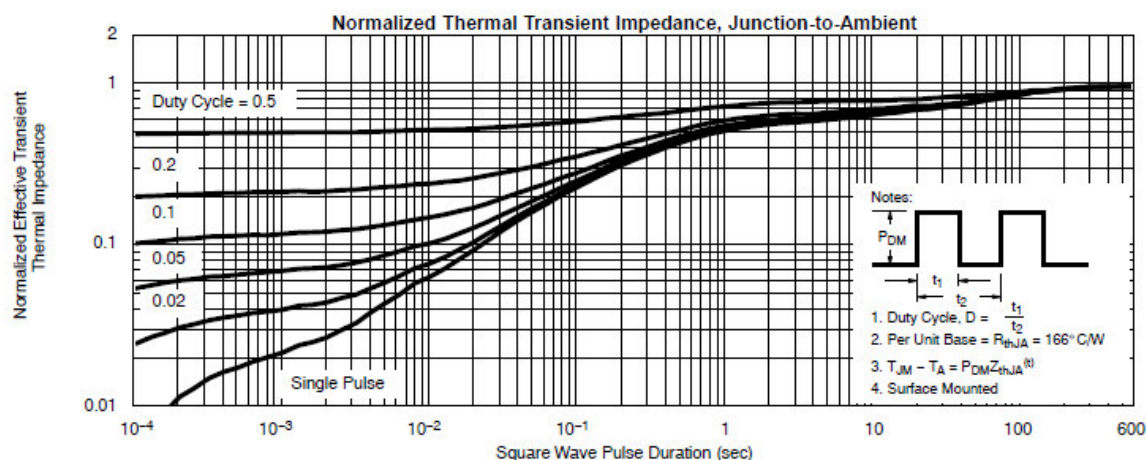
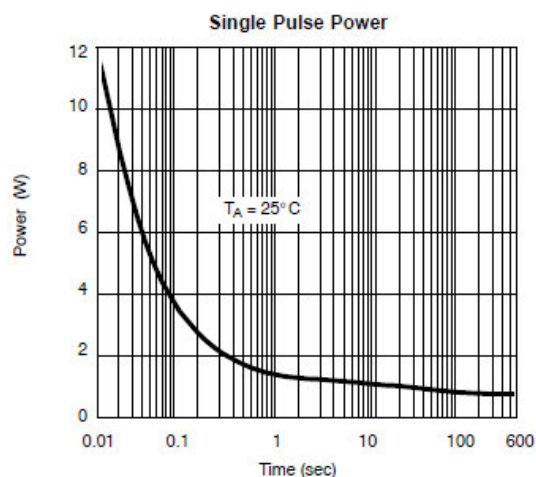
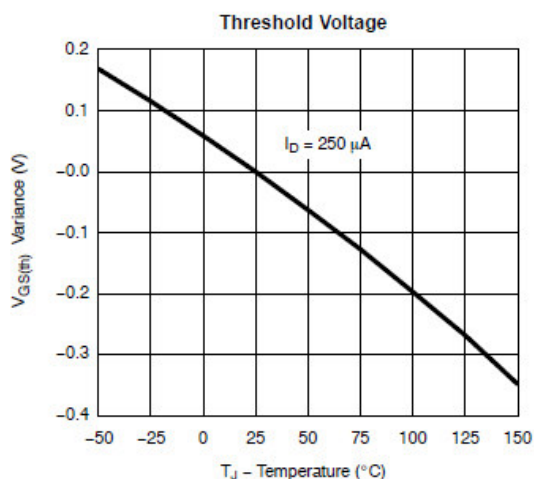
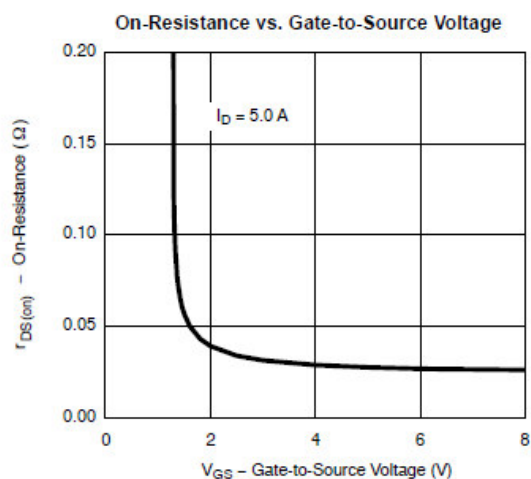
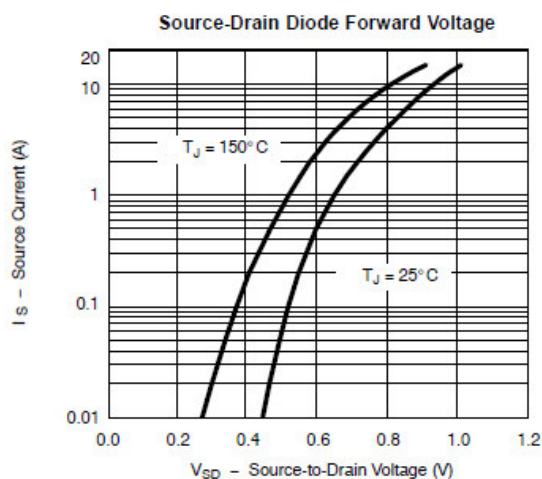


Typical Characteristics





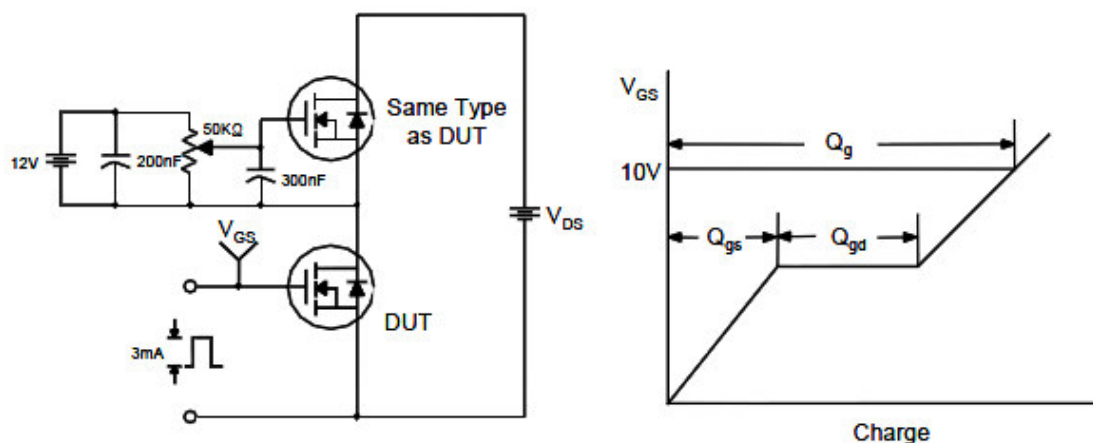
Typical Characteristics



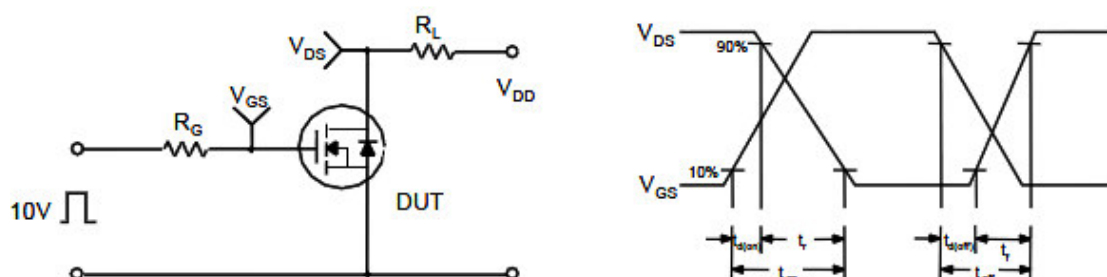


Typical Characteristics

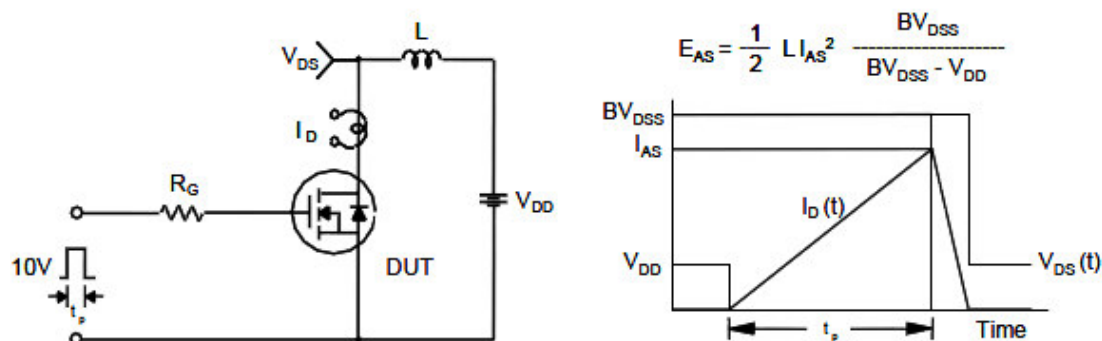
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

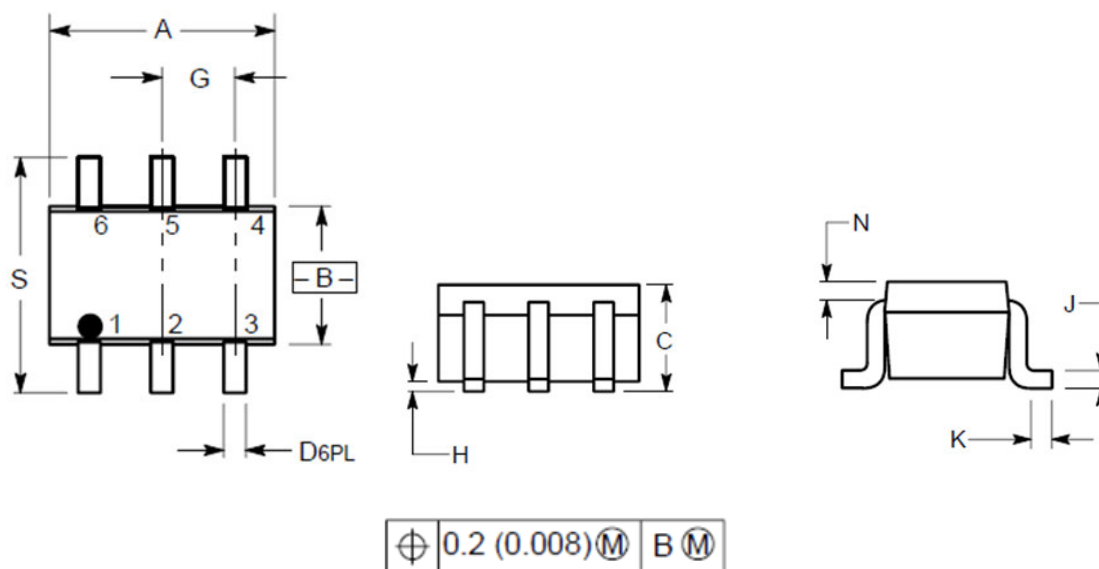


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (SOT-363)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

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